Semiconductor Device Set - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-00-409-9764

Inclosure Mater	al:
Metal all transisto	or and the second se
Overall Length:	
0.170 inches all	transistor and 0.210 inches all transistor
Terminal Length	:
0.500 inches all	transistor
Overall Diamete	r:
0.209 inches all	transistor and 0.230 inches all transistor
Internal Configu	ration:
Junction contact	all transistor
Joint Electronic	Device Engineering Council/jedec/case Outline Designation:
To-18 all transiste	n
Internal Junctio	n Configuration:
Npn all transistor	
Component Fur	ction Relationship:
Matched	
Component Nar	ne And Quantity:
8 transistor	
Mounting Metho	d:
Terminal all trans	istor
Terminal Circle	Diameter:
0.100 inches all	transistor
Semiconductor	Material:
Silicon all transis	tor
Voltage Rating	n Volts Per Characteristic:
40.0 breakdown	voltage, collector-to-emitter, base open all transistor
Current Rating	Per Characteristic:
800.00 milliampe	res source cutoff current all transistor and 10.00 nanoamperes zero-gate-voltage source current preset all transistor
Power Rating P	er Characteristic:
500.0 milliwatts s	mall-signal input power, common-collector absolute all transistor
Transfer Ratio:	
40.0 static forwa	rd current transfer ratio, common-emitter all transistor
Maximum Opera	ting Tempurature Per Measurement Point:
150.0 degrees ce	elsius junction all transistor
Terminal Type A	Ind Quantity:
3 uninsulated wir	e lead all transistor
Shelf Life:	
N/a	
Unit Of Measure	e de la companya de l
Demilitarization	
No	

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